



JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

SOT-23 Plastic-Encapsulate Diodes

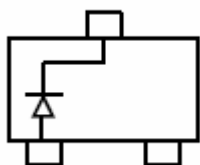
MMBD914LT1 SWITCHING DIODES

FEATURES

Power Dissipation

PD : 225 mW (Tamb=25℃)

SOT-23



MARKING: 5D

Maximum Ratings @T_A=25

Parameter	Symbol	Limits	Unit
Peak Repetitive Peak reverse voltage	V _{RRM}	75	V
Working Peak Reverse Voltage	V _{RWM}		
DC Blocking Voltage	V _R		
Forward Continuous Current	I _{FM}	200	mA
Power Dissipation	Pd	225	mW
Storage temperature	T _{STG}	-55-150	℃

Electrical Characteristics@T_A=25℃

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Reverse Breakdown Voltage	V _{(BR)R}	75			V	I _R =100μA
Forward voltage	V _{F1}			715	mV	I _F =1mA
	V _{F2}			855	mV	I _F =10mA
	V _{F3}			1000	mV	I _F =50mA
	V _{F4}			1250	mV	I _F =150mA
Reverse current	I _{R1}			1	uA	V _R =75V
	I _{R2}			25	nA	V _R =20V
Diode Capacitance	C _D			20	pF	V _R =0V,f=1MHz
Reverse Recovery Time	t _{rr}			4	nS	I _F =I _R =10mA V _R =5V,R _C =100Ω

Typical Characteristics

MMBD914LT1

